

# HCO65S08D1

## eSiC Silicon Carbide Schottky Diode

650 V, 8 A

### Features

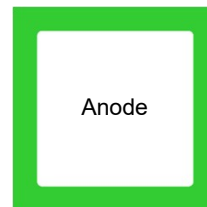
- No reverse recovery current
- Low forward voltage
- 175°C Max junction temperature
- High surge current capability
- Switching behavior independent of temperature

$V_{RRM}$	$I_F$	$T_{J,max}$	$Q_C$
650 V	8 A	175 °C	32 nC

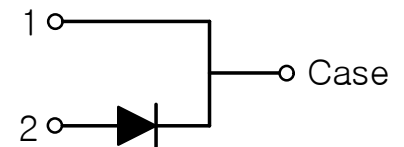
### Applications

- Power Factor Correction
- Industrial Power Supplies
- Solar Inverter, UPS

### Die Configuration



\*Cathode : Bottom



### Die Mechanical Parameters

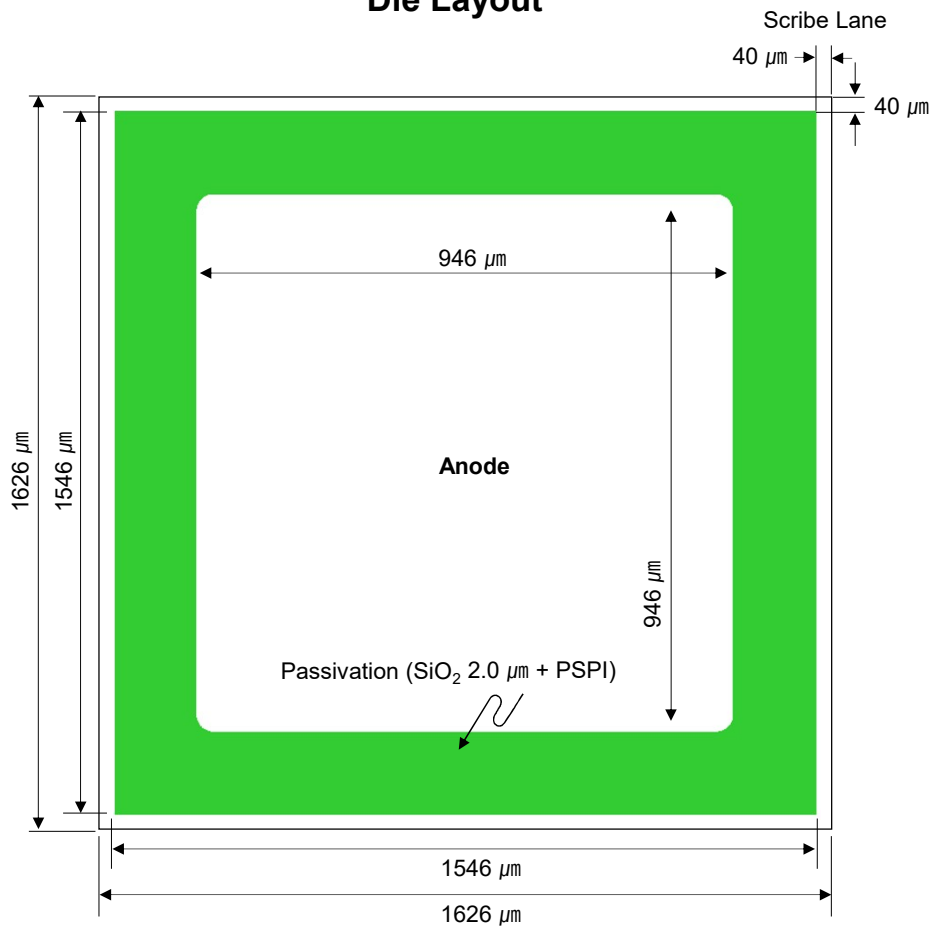
Parameter	Typical Value	Unit
Wafer Diameter	6	inch
Die Dimensions (W x L x T)	1626 x 1626 x 180	$\mu\text{m}$
Anode Metallization (AlCu)	4	$\mu\text{m}$
Bottom Cathode Metallization (Ti/Ni/Ag)	0.5	$\mu\text{m}$
Recommended Source Bond Wire	Al 6mils x 2	ea
Gross Die (Single chip of wafer)	6,030	ea

### Electrical Characteristics ( $T_J = 25^\circ\text{C}$ ) (Note1)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$V_F$	Forward Voltage	$I_F = 8 \text{ A}, T_C = 25^\circ\text{C}$		1.30	1.60	V
$I_R$	Reverse Current	$V_R = 650 \text{ V}, T_C = 25^\circ\text{C}$		-	100	$\mu\text{A}$

1. Based on TO220 package.

### Die Layout



### Wafer Sawing Information

